

August 2000 PRELIMINARY

FDS7764A

30V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{\text{DS(ON)}}$ in a small package.

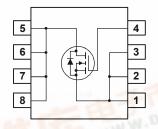
Applications

- Synchronous Rectifier
- DC/DC converter

Features

- 15 A, 30 V. $R_{DS(ON)} = 7.5 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low R_{DS(ON)} High power and current handling capability





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter	F9/(6) =	Ratings	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±12	V
I _D	Drain Current - Continuous	(Note 1a)	15	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	401
		(Note 1c)	1.0	C.C.C
T _J , T _{STG}	Operating and Storage Junction Temperat	ure Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	50 (10 sec)	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

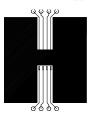
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
FDS7764A	FDS7764A	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		l	I		I
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μА
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 12 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -12 V , V _{DS} = 0 V			-100	nA
On Chara	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	8.0	1.2	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 4.5 V, I _D = 15 A V _{GS} = 10 V, I _D = 15.5 A V _{GS} = 4.5 V, I _D = 15 A, T _J = 125°C		6.0 5.3 9.0	7.5 13.0	mΩ
I _{D(on)}	On-State Drain Current	V _{GS} = 4.5 V, V _{DS} = 5 V	50			Α
g FS	Forward Transconductance	V _{DS} = 10 V, I _D = 15 A		75		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		5070		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		550		pF
C _{rss}	Reverse Transfer Capacitance]		230		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		17	25	ns
t _r	Turn-On Rise Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω		18	25	ns
$t_{d(off)}$	Turn-Off Delay Time			69	100	ns
t _f	Turn-Off Fall Time			29	42	ns
Qg	Total Gate Charge	V _{DS} = 15 V, I _D = 15 A,		33	46	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		7.5		nC
Q _{gd}	Gate-Drain Charge			6.8		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage		0.7	1.2	V	

Notes

1. R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



a) 50°/W when mounted on a 1in² pad of 2 oz copper



b) 105°/W when mounted on a .04 in² pad of 2 oz copper



c) 125°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

Typical Characteristics

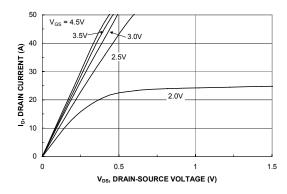


Figure 1. On-Region Characteristics.

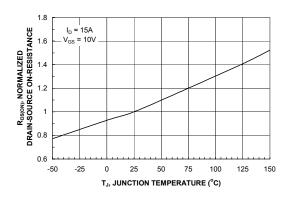


Figure 3. On-Resistance Variation with Temperature.

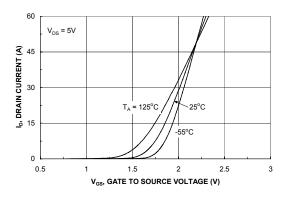


Figure 5. Transfer Characteristics.

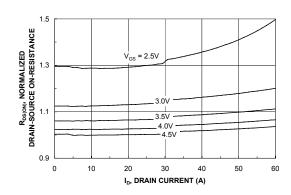


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

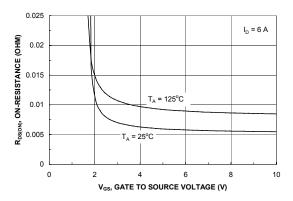


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

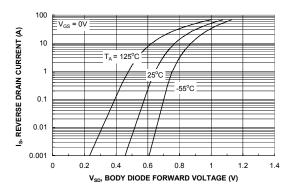
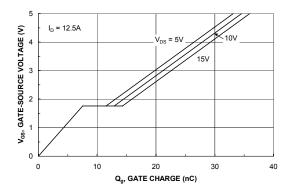


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



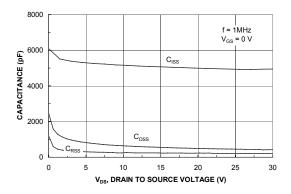


Figure 7. Gate Charge Characteristics.

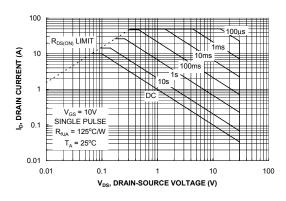


Figure 8. Capacitance Characteristics.

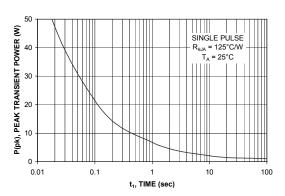


Figure 9. Maximum Safe Operating Area.



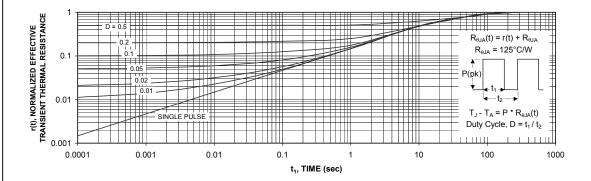
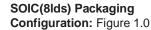


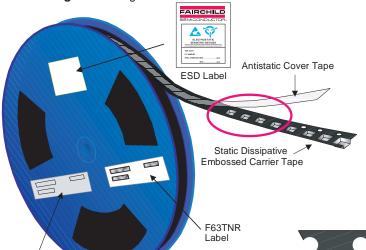
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions



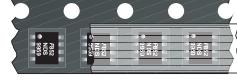




Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 330m diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts





Packaging Option no flow code) Packaging type Rail/Tube TNR TNR Qty per Reel/Tube/Bag 2,500 95 4,000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343x64x343 530x130x83 343x64x343 184x187x47 Max qty per Box 5,000 30,000 8,000 1,000

SOIC (8lds) Packaging Information

Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

SOIC-8 Unit Orientation

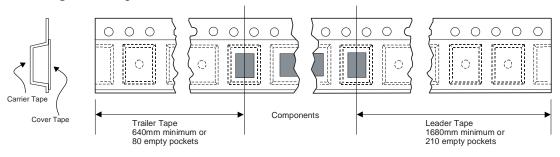
F63TNR Label sample

Customized



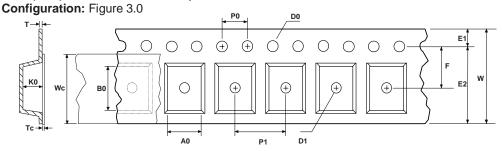
343mm x 342mm x 64mm Standard Intermediate box ESD Label F63TN Label

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0



SO-8 Tape and Reel Data and Package Dimensions, continued

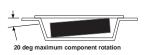
SOIC(8lds) Embossed Carrier Tape



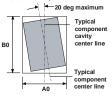
User Direction of Feed	
	$\overline{}$

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



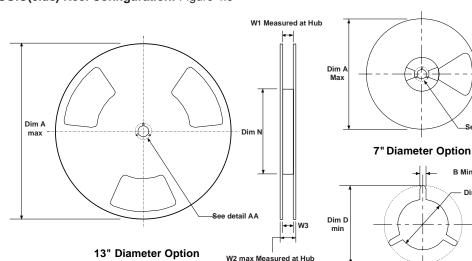
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

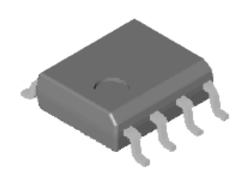
SOIC(8lds) Reel Configuration: Figure 4.0

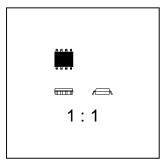


								DETAIL AA	1
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SO-8 Tape and Reel Data and Package Dimensions, continued

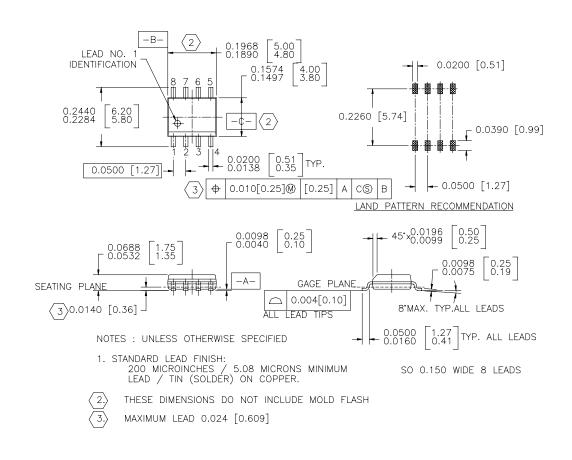
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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